## PF0146

# MOS FET Power Amplifier Module for GSM Handy Phone HITACHI 

## Application

For GSM class4 890 to 915 MHz

## Features

－Small package： $1 \mathrm{cc}, 3 \mathrm{~g}$
－High efficiency：50\％Typ
－High speed switching： $0.9 \mu \mathrm{sec}$
Pin Arrangement
－RF－E

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## Internal Diagram and External Condition at Classification


$\mathrm{C} 1=0.01 \mu \mathrm{~F}$ (Ceramic chip)
$\mathrm{C} 2=220 \mu \mathrm{~F}$ (Aluminum electrolyte)
$\mathrm{FB}=$ Ferrite bead BLO1RN1-A62-001 (Manufacture: MURATA) or equivalent $\mathrm{Z} 1=\mathrm{Z} 2=50 \Omega$ (Microstrip line)

Absolute Maximum Ratings $\left(\mathrm{Tc}=25^{\circ} \mathrm{C}\right)$

| Item | Symbol | Rating | Unit |
| :--- | :--- | :--- | :--- |
| Supply voltage | VDD | 10 | V |
| Supply current | IDD | 3 | A |
| APC voltage | VAPC | 6 | V |
| Input power | Pin | 20 | mW |
| Operating case temperature | Tc $(\mathrm{op})$ | -30 to +100 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | Tstg | -30 to +100 | ${ }^{\circ} \mathrm{C}$ |
| Output power | Pout | 7 | W |

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Electrical Characteristics $\left(\mathrm{Tc}=25^{\circ} \mathrm{C}\right)$

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Frequency range | f | 890 | - | 915 | MHz | - |
| Control voltage range | VAPC | 0.5 | - | 4.0 | V | - |
| Drain cutoff current | IDS | - | - | 100 | $\mu \mathrm{A}$ | $\mathrm{VDD}=10 \mathrm{~V}, \mathrm{VAPC}=0 \mathrm{~V}$ |
| Total efficiency | $\eta \mathrm{T}$ | 45 | 50 | - | \% | $\mathrm{Pin}=2 \mathrm{~mW}, \mathrm{VDD}=6 \mathrm{~V}$, |
| 2nd harmonic distortion | 2nd H.D. | - | -50 | -35 | dBc | Pout = 3.2 W (at APC controlled), |
| 3rd harmonic distortion | 3rd H.D. | - | -60 | -45 | dBc | $\mathrm{RL}=\mathrm{Rg}=50 \Omega, \mathrm{Tc}=25^{\circ} \mathrm{C}$ |
| Input VSWR | VSWR (in) | - | 2 | 3 | - |  |
| Output power (1) | Pout (1) | 3.6 | 4.2 | - | W | $\begin{aligned} & \mathrm{Pin}=2 \mathrm{~mW}, \mathrm{VDD}=6 \mathrm{~V}, \\ & \mathrm{VAPC}=4 \mathrm{~V}, \mathrm{RL}=\mathrm{Rg}=50 \Omega, \\ & \mathrm{TC}=25^{\circ} \mathrm{C} \end{aligned}$ |
| Output power (2) | Pout (2) | 2.4 | 3.0 | - | W | $\begin{aligned} & \mathrm{Pin}=2 \mathrm{~mW}, \mathrm{VDD}=5.4 \mathrm{~V}, \\ & \mathrm{VAPC}=4 \mathrm{~V}, \mathrm{RL}=\mathrm{Rg}=50 \Omega, \\ & \mathrm{TC}=80^{\circ} \mathrm{C} \end{aligned}$ |
| Isolation | - | - | -45 | -40 | dBm | $\begin{aligned} & \mathrm{Pin}=2 \mathrm{~mW}, \mathrm{VDD}=6 \mathrm{~V}, \\ & \mathrm{VAPC}=0.5 \mathrm{~V}, \mathrm{RL}=\mathrm{Rg}=50 \Omega, \\ & \mathrm{Tc}=25^{\circ} \mathrm{C} \end{aligned}$ |
| Switching time | tr, tf | - | 0.9 | 2 | $\mu \mathrm{s}$ | $\begin{aligned} & \text { Pin }=2 \mathrm{~mW}, \mathrm{VDD}=6 \mathrm{~V}, \\ & \text { Pout }=3.2 \mathrm{~W}, \mathrm{RL}=\mathrm{Rg}=50 \Omega, \\ & \mathrm{Tc}=25^{\circ} \mathrm{C} \end{aligned}$ |
| Stability | - | No parasitic oscillation |  |  | - | $\begin{aligned} & \text { Pin }=2 \mathrm{~mW}, \mathrm{VDD}=7.5 \mathrm{~V} \text {, } \\ & \text { Pout } \leq 3.2 \mathrm{~W} \text { (at APC controlled), } \\ & \text { Rg }=50 \Omega, \mathrm{Tc}=25^{\circ} \mathrm{C}, \\ & \text { Output VSWR }=10: 1 \text { All phases } \end{aligned}$ |

## Test System Diagram



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## Switching Time Test Diagram



## Test Fixture Pattern



## Note for Use

- Apply control voltage range as VAPC $=0.5$ to 4.0 V , and GSM burst mode must be applied to all operation. For instance, pulse width $=0.577 \mathrm{msec}$., duty $=12.5 \%$ and $\mathrm{VAPC} \leq 0.5 \mathrm{~V}$, for all 4.616 msec . Frame except for 0.577 msec . pulse.
- Unevenness and distortion at the surface of PCB mounted module should be as small as possible.
- To protect devices from electro-static damage, soldering iron, measuring equipment and human body, etc. should be grounded.
- To avoid the degradation of efficiency and output power, lead pins should not be floated from copper foil of PCB, and connected to right position of RF signal line (refer to figure 1)
- Recommendation to improve the thermal resistance is shown below.
- Make through holes as many as possible under module.
- Use heat sink on the top case of module.
- When the external components(Isolator, Duplexer, etc) of the module are changed, the electrical characteristics of total system should be evaluated enough.
- To avoid destruction of module caused by excess power consumption, voltage of APC should be limited less than 6 V .
- To get good stability, all GND pins should be soldered to ground pattern of PCB.
- Don' t apply Full Heating Methods except Infrared Heating Methods.
- In case of Partial Heating Methods, soldering temperature and time should be less than $230^{\circ} \mathrm{C}, 10 \mathrm{sec}$, per each GND pin.
- Soldering temperature and time for I.R. Reflow should be the reflow profile shown in figure 2.
- Recommended conditions for Rising Methods shows as follows.

Solvents: de-ionized water, isopropyl alcohol, ethyl alcohol
Rising condition: in case of soak rising 5 min max, in case of ultrasonic rising 5 min max

- Don' t apply dipping solder method to mount.
- Apply the way of washing after actual confirmation.
- Recommended pattern of footprint is shown in figure 3.


Figure 1

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Figure 2


Figure 3

## Characteristics Curve



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## Package Dimensions

Unit: mm


